

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	4880	semiconductor and (CMOS or complementary or (NMOS same PMOS)) and ((lattice near constant) or strain\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/06/10 13:25
S2	1897	semiconductor and (CMOS or complementary or (NMOS same PMOS)) and (((lattice near constant) or strain\$3) with (silicon or si or germanium or ge or carbon or c))	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/06/10 16:42
S9	2280	semiconductor and (CMOS or complementary or (NMOS same PMOS)) and (((lattice near3 constant) or strain\$3) with (silicon or si or germanium or ge or carbon or c))	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/06/10 16:43
S10	803	(257/338 or 257/351).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/06/10 16:45
S11	32	(257/338 or 257/351).ccls. and (((lattice near3 constant) or strain\$3) with (silicon or si or germanium or ge or carbon or c))	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/06/10 16:46
S12	59	(257/368 or 257/369).ccls. and (((lattice near3 constant) or strain\$3) with (silicon or si or germanium or ge or carbon or c))	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/06/10 16:46
S13	150	(257/376 or 257/616).ccls. and (((lattice near3 constant) or strain\$3) with (silicon or si or germanium or ge or carbon or c))	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/06/10 16:46
S14	21	(257/617).ccls. and (((lattice near3 constant) or strain\$3) with (silicon or si or germanium or ge or carbon or c))	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/06/10 16:46